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Form PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 5347-208	Serial No. 09/891,552
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicants: Gerald Lucovsky et al.	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
		Wilk et al., <i>High-K Gate Dielectrics: Current Status and Materials Properties Considerations</i> , Journal of Applied Physics, Vol. 89, No. 10, May 15, 2001, pp. 5243-5275	
		Lucovsky et al., <i>Microscopic Model for Enhanced Dielectric Constants in Low Concentration SiO₂-Rich Noncrystalline Zr and Hf Silicate Alloys</i> , Applied Physics Letters, Vol. 77, No. 18, October 30, 2000, pp. 2912-2914	
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	5	Gusev et al., <i>High-Resolution Depth Profiling in Ultrathin Al₂O₃ Films on Si</i> , Applied Physics Letters, Vol. 76, No. 2, January 10, 2000, pp. 176-178	
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	12	Yasuda et al., <i>Low-Temperature Formation of Device-Quality SiO₂/Si Interfaces by a Two-Step Remote Plasma-Assisted Oxidation/Deposition Process</i> , J. Vac. Sci. Technol. B, Vol. 10, No. 4, July/August 1992, pp. 1844-1851	
	13	Hersee et al., <i>The Operation of Metalorganic Bubblers at Reduced Pressure</i> , J. Vac. Sci. Technol. A, Vol. 8, No. 2, March/April 1990, pp. 800-804	
	14	Hunt et al., <i>The Absolute Determination of Resonant Energies for the Radiative Capture of Protons by Boron, Carbon, Fluorine, Magnesium, and Aluminum in the Energy Range Below 500 kev</i> , Physical Review, Vol. 89, No. 6, March 15, 1953, pp. 1283-1287	

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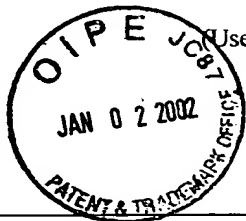
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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate

FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation Yes No

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Qu	1.	Gordon et al., "Chemical Vapor Deposition and Properties of Amorphous Aluminum Oxide Films," Material Research Society Symposium Proceedings, 446, December 2-4, 1996, 383-388.
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